ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE2366
Silicon PNP Transistor
High Voltage Video Amp
(Compl to NTE399)

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 300V

Collector–Emitter Voltage, V_{CEO} 300V

Emitter–Base Voltage, V_{EBO} 5V

Collector Current, I_C

Continuous 100mA

Peak 200mA

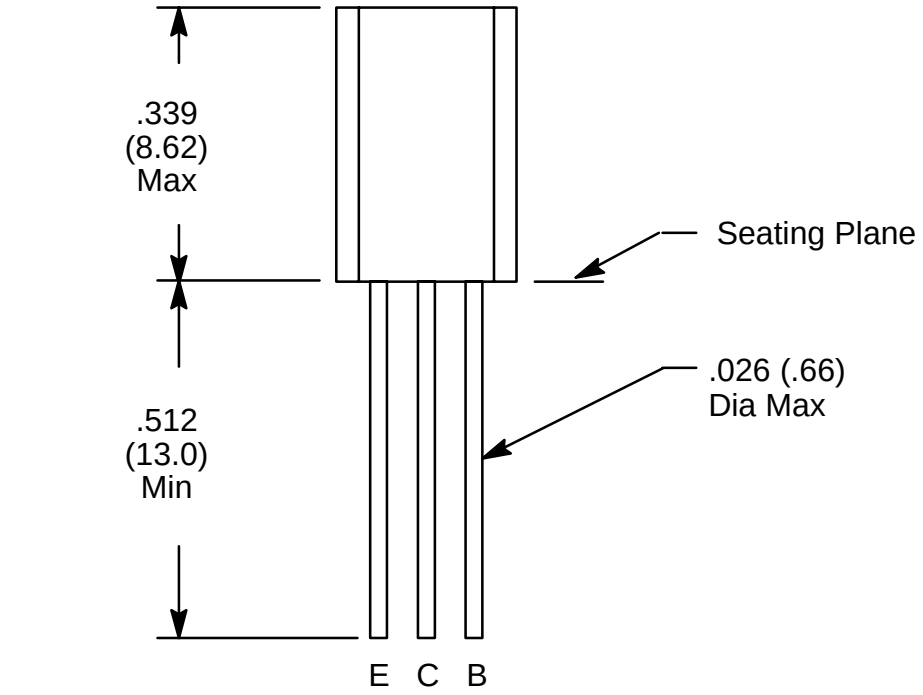
Power Dissipation, P_C 1.0W

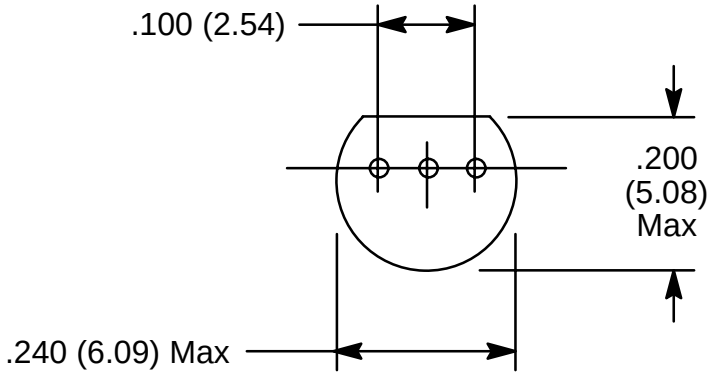
Operating Junction Temperature, T_j . . . . . +150°C

Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 200V, I_E = 0	–	–	0.1	µA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0	–	–	0.1	µA
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10µA, I_E = 0	300	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA, R_{BE} = ∞	300	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10µA, I_C = 0	5	–	–	V
DC Current Gain	h_{FE}	V_{CE} = 10V, I_C = 10mA	40	–	320	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 20mA, I_B = 2mA	–	–	0.6	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 20mA, I_B = 2mA	–	–	1.0	V
Current Gain–Bandwidth Product	f_T	V_{CE} = 30V, I_C = 10mA	–	150	–	MHz
Capacitance	C_{ob}	V_{CB} = 30V, f = 1MHz	–	2.6	–	pF
Reverse Transfer Capacitance	C_{re}	V_{CB} = 30V, f = 1MHz	–	1.8	–	pF


.339
(8.62)
Max
Seating Plane
.026 (.66)
Dia Max
.512
(13.0)
Min
E C B


.100 (2.54)
.200
(5.08)
Max
.240 (6.09) Max